

Form PTO-1449 (modified)

Atty. Docket No.
102-0072US-4Serial No.
09/923,058

List of Patents and Publications for Applicant's

Inventor/Applicant:

Becker, et al. / Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

Title: METHODS FOR ENHANCING SILICON
DIOXIDE TO SILICON NITRIDE
SELECTIVITY (as previously amended)Filing Date:
08/06/01Group:
1763

(Use several sheets if necessary)

U.S. Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date of App.
<i>gag</i>	A82	3,653,898	4/4/72	Shaw	96	35	
	A83	3,904,454	9/9/75	Magdo et al.	156	11	
	A84	4,135,954	1/23/79	Chang et al.	148	187	
	A85	4,243,435	1/6/81	Barile et al.	148	1.5	
	A86	4,696,097	9/29/87	McLaughlin et al.	437	193	
	A87	4,832,789	5/23/89	Cochran et al.	156	644	
	A88	4,837,176	6/6/89	Zdebel et al.	437	31	
	A89	4,030,967	6/21/77	Ingrey et al.	156	643	
	A90	4,671,849	6/9/87	Chen et al.	156	643	
	A91	5,312,518	5/17/94	Kadomura	156	662	5/29/92
	A92	6,399,514	6/4/02	Marks et al.	438	729	8/24/00
	A93	4,883,767	11/28/89	Gray et al.	437	41	
	A94	4,962,058	10/9/90	Cronin et al.	437	187	
	A95	5,136,124	8/4/92	Cronin et al.	174	261	9/19/1990
	A96	5,169,802	12/8/92	Yeh	437	195	6/17/91
	A97	5,189,506	2/23/93	Cronin et al.	257	752	6/3/92
	A98	5,354,711	10/11/94	Heitzmann et al.	437	182	7/8/93
<i>gag</i>	A99	6,171,974	1/9/01	Marks et al.	438	740	1/24/92

Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No
	B	n/a					

EXAMINER:

George Goudreau

DATE CONSIDERED:

3-05'

EXAMINER: INITIAL IF REFERENCE CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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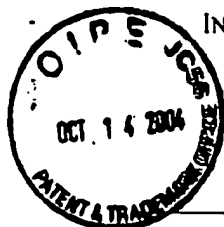
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Other Art (Including Author, Title, Date Pertinent Pages, Etc.)

Exam. Init.	Ref. Des.	Citation
	C77	Various Japanese abstracts (untranslated) 8p-P-14, 8p-P-15, 8a-R-1
	C78	Various Japanese abstracts (untranslated) 7p-T-14, 7p-T-15, 7p-T-16
gag	C79	H. Enomoto & T. Tokunaga, "Analysis of Mechanisms of Highly Selective Oxide Etching," 1994 Dry Process Symposium, pp. 241-46 (Nov. 10-11, 1994, Tokyo).
	C80	Y. Gotoh & T. Kure, "Analysis of Polymer Formation During SiO ₂ Microwave Plasma Etching," 1994 Dry Process Symposium, pp. 211-16 (Nov. 10-11, 1994, Tokyo).
	C81	Y. Hikosaka et al., "Inductively-Coupled Plasma Etching in a Pulsed Mode," 1994 Dry Process Symposium, pp. 199-204 (Nov. 10-11, 1994, Tokyo).
	C82	K. Kurihara et al., "Measurement of Energy Distribution of Ion Species Through a High-Aspect-Ratio Hole in a C4F8 Plasma," 1994 Dry Process Symposium, pp. 217-221 (Nov. 10-11, 1994, Tokyo).
	C83	Shin Arai, "Polymer Deposition Control in SiO ₂ Etching by Substrate Temperature Manipulation," 1994 Dry Process Symposium, pp. 223-227 (Nov. 10-11, 1994, Tokyo).
	C84	Reply and Counterclaims in Reply to Counterclaim and Demand for Jury Trial, Motorola, Inc. v. Micron Technology, Inc., Civ. No. 04 CA 007 LY (Apr. 7, 2004) (W.D. Tex.).
gag	C85	J.L. Yeh et al., "Reverse Pillar—A Self-Aligned and Self-Planarised Metallisation Scheme for Sub-Micron Technology," Vacuum: Technology, Applications & Ion Physics, Vol. 38, Nos. 8-10, pp. 817-821 (1988).

* These references are not properly cited. They lack reference to the publication date, author, and the source of this material for each of the abstracts printed in Japanese. This information should be provided to the examiner in English on a 1449 form for review by the examiner.

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